

Preliminary

Notice: This is not a final specification.
Some parametric limits are subject to change.

M5M29KB/T641AVP

67,108,864-BIT (8,388,608-WORD BY 8-BIT /4,194,304-WORD BY 16-BIT)
CMOS 3.3V-ONLY, BLOCK ERASE FLASH MEMORY

DESCRIPTION

The M5M29KB/T641AVP are 3.3V-only high speed 67,108,864-bit CMOS boot block FLASH Memories with alternating BGO(Back Ground Operation) feature. The BGO feature of the device allows Program or Erase operations to be performed in one bank while the device simultaneously allows Read operations to be performed on the other bank.

This BGO feature is suitable for mobile and personal computing, and communication products.

The M5M29KB/T641AVP are fabricated by CMOS technology for the peripheral circuit and DINOR IV(Divided bit-line NOR IV) architecture for the memory cell, and are available in 48pin TSOP(I) for lead free use.

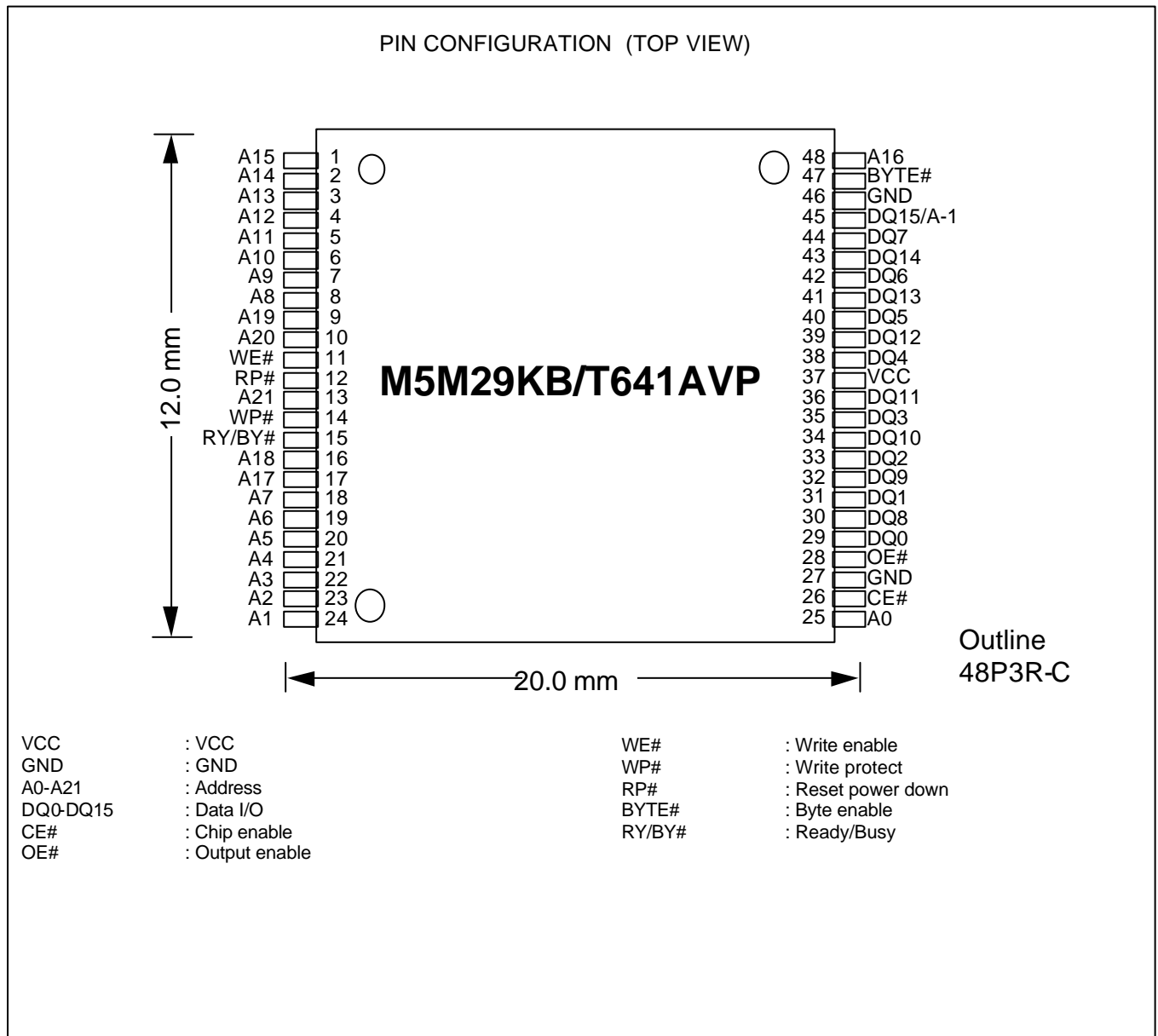
M5M29KB/T641AVP provides for Software Lock Release function. Usually, all memory blocks are locked and can not be programmed or erased, when WP# is low. Using Software Lock Release function, program or erase operation can be executed.

FEATURES

Access time	Flash	70ns (Max.)
Supply voltage		VCC= 3.0 ~ 3.6V
Ambient temperature		Ta=-40 ~ 85 °C
Package	48pin TSOP(Type-I), Lead pitch 0.5mm	
	Outer-lead finishing : Sn-Cu	

APPLICATION

Digital Cellar Phone, Telecommunication,
PDA, Car Navigation System, Video Game Machine



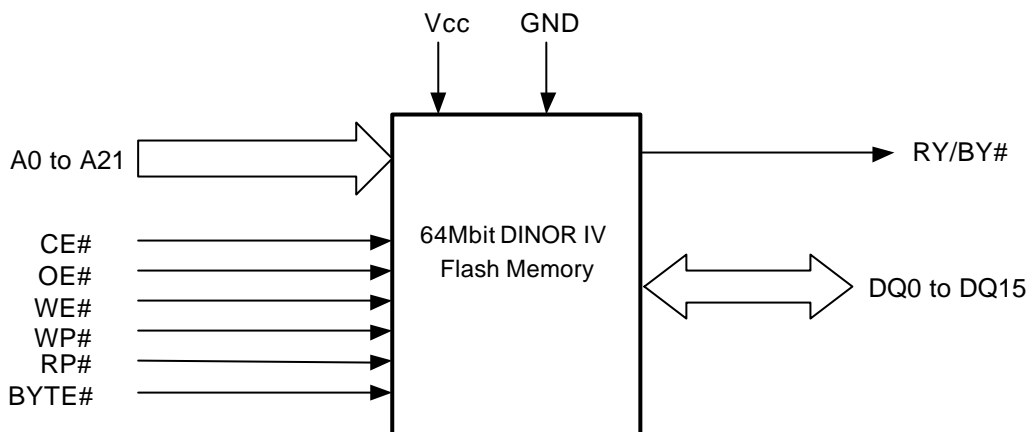
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64M Flash Memory Block Diagram



Capacitance

Symbol	Parameter		Conditions	Limits			Unit
				Min.	Typ.	Max.	
CIN	Input capacitance	A21-A0, OE#, WE#, CE#, WP#, RP#, BYTE#	Ta=25°C, f=1MHz, Vin=Vout=0V			12	pF
COUT	Output Capacitance	DQ15-DQ0, RY/BY#				12	pF

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